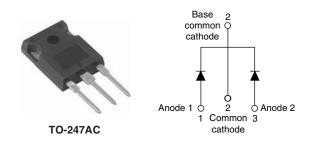
VS-60CPU02-F, VS-60CPU02-N3

Vishay Semiconductors

Ultrafast Rectifier, FRED Pt[®], 2 x 30 A



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PRODUCT SUMMARY							
Package	TO-247AC						
I _{F(AV)}	2 x 30 A						
V _R	200 V						
V _F at I _F	0.75 V						
t _{rr} typ.	30 ns						
T _J max.	175 °C						
Diode variation	Common cathode						

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- · Designed and qualified according to JEDEC[®]-JESD 47
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

VS-60CPU02... series are the state of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, welding, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.





ABSOLUTE MAXIMUM RATI	NGS				
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Repetitive peak reverse voltage		V _{RRM}		200	V
Average rectified forward current	per leg	I =		30	
p	er device	I _{F(AV)}	Rated V _R , T _C = 145 °C	60	А
Non-repetitive peak surge current per leg		I _{FSM}	T _J = 25 °C	300	~
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 137 °C	60	
Operating junction and storage temperate	ures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL TEST CONDITIONS MIN. TYP. MAX.								
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-				
	V _F	I _F = 30 A	-	0.92	1.1	V			
Forward voltage		I _F = 30 A, T _J = 150 °C	-	0.75	0.85				
	I _R	V _R = V _R rated	-	-	50				
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	30	300	μΑ			
Junction capacitance	CT	V _R = 200 V	-	100	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	12	-	nH			

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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		I _F = 1.0 A, dI _F /dt =	100 A/ μ s, V _R = 30 V	-	30	36			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	30	-	ns		
		T _J = 125 °C		-	47	-			
Pook recovery ourrent	I _{RRM}	T _J = 25 °C	I _F = 30 A dI _F /dt = - 200 A/μs V _R = 160 V	-	3	-	A		
Peak recovery current		T _J = 125 °C		-	6.5	-			
Reverse recovery charge	0	T _J = 25 °C		-	42	-			
	Q _{rr}	T _J = 125 °C		-	160	-	nc		

THERMAL - MECHANICAL SPECIFICATIONS ($T_J = 25$ °C unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction to case per leg	R _{thJC}		-	0.6	1.0				
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	40	°C/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Woight			-	6.0	-	g			
Weight			-	0.21	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ⋅ cm (lbf ⋅ in)			
Marking device		Case style TO-247AC	60CPU02						

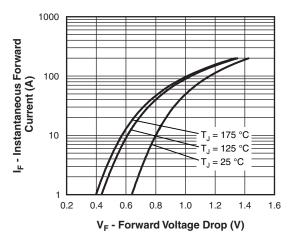
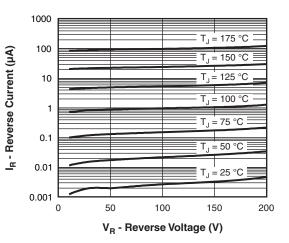
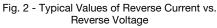


Fig. 1 - Typical Forward Voltage Drop Characteristics





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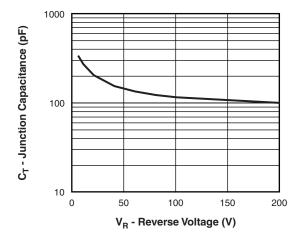


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

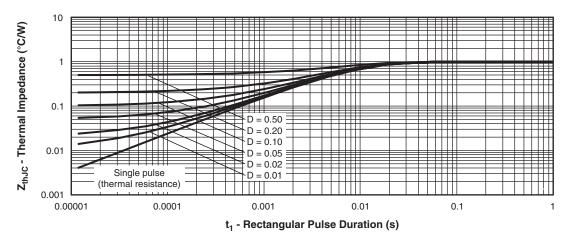


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

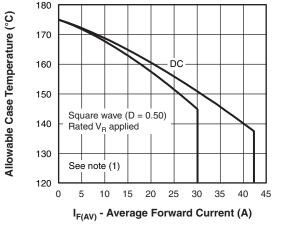


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

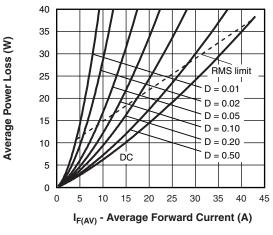


Fig. 6 - Forward Power Loss Characteristics

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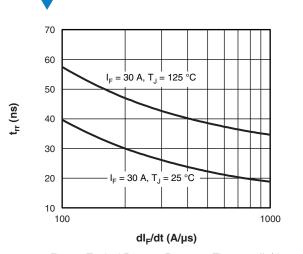
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Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

Note

SHA

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

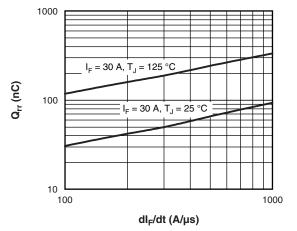


Fig. 8 - Typical Stored Charge vs. dI_F/dt

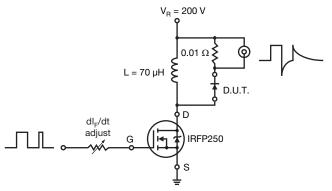
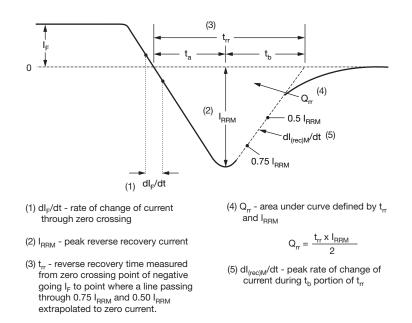
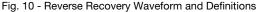


Fig. 9 - Reverse Recovery Parameter Test Circuit





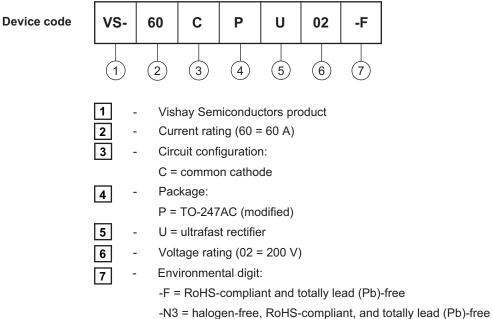
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ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)									
PREFERRED P/N	FERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION								
VS-60CPU02-F	25	500	Antistatic plastic tube						
VS-60CPU02-N3	25	500	Antistatic plastic tube						

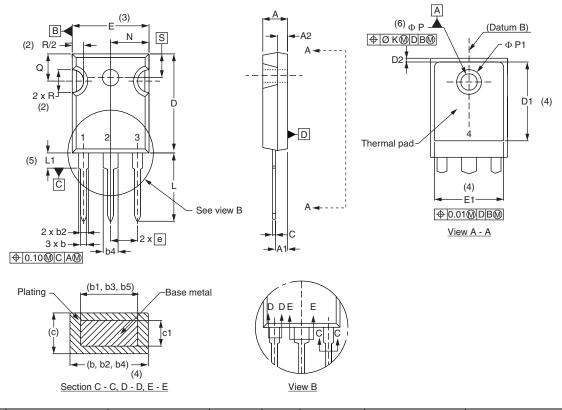
LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95542						
Part marking information	www.vishay.com/doc?95007					





TO-247 - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	NOTES SYMBOL	SVMBOI	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
A	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			Е	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	-	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØК	0.2	254	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ØР	3.56	3.66	0.14	0.144	
с	0.38	0.89	0.015	0.035			Ø P1	-	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

⁽⁶⁾ Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-247 with exception of dimension c and Q

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